

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Cancel non-elected claims 1-12.

13. (Currently Amended) A method of manufacturing a field emission device, the method comprising:

(a) forming a field emission array including an electron emission source for emitting electrons and a gate electrode having a gate hole through which the electrons pass, on a substrate;

(b) ~~manufacturing~~ providing an additional mesh grid in which an electron-controlling hole corresponding to the gate hole is formed;

(c) thermally expanding the substrate on which the field emission array is formed and the mesh grid to be fixed onto the substrate;

(d) fixing the thermally-expanded mesh grid onto the substrate using a tension member that applies a tensile force to the mesh grid; and

(e) cooling the substrate and the mesh grid at room temperature.

14. (Original) The method of claim 13, wherein in (c), the rear plate and the field emission array are heated at a temperature higher than an operating temperature of the field emission array.

15. (Original) The method of claim 13, wherein in (a), a fixing pad for fixing the tension member is formed on the substrate.

16. (Original) The method of claim 13, wherein in (b), a grid insulating layer is formed at least one side of the mesh grid.

17. (Original) The method of claim 16, wherein the grid insulating layer is formed of one material selected from amorphous silicon and silicon oxide.

18. (Currently Amended) A method of manufacturing a field emission display, the method comprising:

a) preparing an anode plate on which an anode electrode and a phosphor layer are formed inside of a front plate;

b) preparing a cathode plate on which a field emission array including an electron emission source for emitting electrons corresponding to the phosphor layer and a gate electrode having a gate hole through which the electrodes pass inside of a rear plate;

c) ~~manufacturing~~ providing an additional mesh grid in which an electron-controlling hole corresponding to the gate hole is formed;

d) thermally expanding the rear plate on which the field emission array is formed and the mesh grid to be fixed onto the rear plate;

e) fixing the thermally-expanded mesh grid onto the substrate using a tension member that applies a tensile force to the mesh grid; and

f) vacuumizing and sealing the anode plate and the cathode plate in the state that a spacer having a predetermined depth is interposed between the cathode plate and the anode plate.

19. (Original) The method of claim 18, wherein in (d), the rear plate and the field emission array are heated at a temperature higher than an operating temperature of the field emission array.

20. (Original) The method of claim 18, wherein in (b), a fixing pad for fixing the tension member is formed on the substrate.

21. (Original) The method of claim 18, wherein in (c), a grid insulating layer is formed at least one side of the mesh grid.

22. (Original) The method of claim 21, wherein the grid insulating layer is formed of one material selected from amorphous silicon and silicon oxide.

23. (Original) The method of claim 18, wherein e) comprises:
fixing the spacer in the anode plate using a binder; and
firing the phosphor layer together with the binder.